L	Hits	Search Text	DB	Time stamp
Number 163	6673	((impurity or doping) adj (density))	USPAT;	2004/09/02
103	0070	((impurity or doping) adj (density))	US-PGPUB;	16:49
			EPO; JPO;	10.40
			DERWENT;	
			IBM_TDB	
164	908	((impurity or doping) adj (density)) and	USPAT;	2004/09/02
		junction and diode	US-PGPUB;	16:49
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
165	212	((impurity or doping) adj (density)) and	USPAT;	2004/09/02
		junction and diode and polysilicon	US-PGPUB;	16:49
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
166	8	((impurity or doping) adj (density)) same	USPAT;	2004/09/02
		junction same diode same polysilicon	US-PGPUB;	16:54
			EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
167	46	((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) same junction same diode	US-PGPUB;	16:54
		same polysilicon	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
168	39	(US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	16:54
		US-6352882-\$ or US-6121661-\$ or	JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT	
		US-6204518-\$ or US-5962900-\$ or		
		US-5907778-\$ or US-5686736-\$ or		
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or	:	
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or		
		(US-20010045665-\$ or US-20020031916-\$ or		
		US-20020057594-\$ or US-20020125541-\$ or		
		US-20020043687-\$ or US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
·		GB-2218565-\$).did.		

170	0	((US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
	_	US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	16:55
İ		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	
		US-5907778-\$ or US-5686736-\$ or	.5	
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		·
		US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		• • • • • • • • • • • • • • • • • • • •		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or		
		(US-20010045665-\$ or US-20020031916-\$ or		
		US-20020057594-\$ or US-20020125541-\$ or		
		US-20020043687-\$ or US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.) and (((impurity or		
		doping) adj (density or concentration))		
		near5 (equal or similar)) same junction		
	_	same diode same polysilicon		
171	0	((US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	16:55
		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	•
		US-5907778-\$ or US-5686736-\$ or		
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or		
1	_	US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or		
		(US-20010045665-\$ or US-20020031916-\$ or		
		US-20020057594-\$ or US-20020125541-\$ or		
		US-20020043687-\$ or US-20020074483-\$ or		
		·		
		US-20020063288-\$).did. or (JP-05283715-\$		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or JP-04034982-\$).did. or (US-5386138-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or JP-04034982-\$).did. or (US-5386138-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or JP-04034982-\$).did. or (US-5386138-\$ or JP-05283715-\$ or JP-2001257349-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$ or JP-07245344-\$ or JP-04069939-\$ or JP-04034982-\$).did. or (US-5386138-\$ or JP-05283715-\$ or JP-2001257349-\$ or GB-2218565-\$).did.) and (((impurity or		

172		((US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	16:55
		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	
		US-5907778-\$ or US-5686736-\$ or		
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or		
		(US-20010045665-\$ or US-20020031916-\$ or		
]	US-20020057594-\$ or US-20020125541-\$ or		
	1	US-20020043687-\$ or US-20020074483-\$ or		
	Ì	US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
	ļ	JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.) and (((impurity or		
		doping) adj (density or concentration))		
		near5 (equal or similar)) and junction and		
		diode same polysilicon		
173	0	1	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB:	16:55
•		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	10.00
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	
		US-5907778-\$ or US-5686736-\$ or		
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or		
		(US-20010045665-\$ or US-20020031916-\$ or		
		US-20020057594-\$ or US-20020125541-\$ or		
		US-20020043687-\$ or US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.) and (((impurity or		
		doping) adj (density or concentration))		

174	0	((US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
174	"	US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	16:55
		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	10.00
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	
	1		IBM_IDB	
	i	US-5907778-\$ or US-5686736-\$ or		
	1	US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$).did. or	•	
		(US-20010045665-\$ or US-20020031916-\$ or		
		US-20020057594-\$ or US-20020125541-\$ or		
		US-20020043687-\$ or US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.) and (((impurity or		
		doping) adj (density or concentration))		
		near10 (equal or similar)) and junction and		
		diode and polysilicon		
175	170	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or similar))	US-PGPUB;	16:56
		and junction and diode and polysilicon	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
176	24	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or	US-PGPUB;	16:56
		similar)).ti,ab,clm. and junction and diode	EPO; JPO;	
		and polysilicon	DERWENT;	
			IBM_TDB	
177	11	(((impurity or doping) adj (density or	USPAT;	2004/09/02
İ		concentration)) near10 (equal or	US-PGPUB;	16:56
		similar)).ti,ab,clm. and junction.ti,ab,clm.	EPO; JPO;	
		and diode and polysilicon	DERWENT;	
			IBM_TDB	
179	0	(((impurity or doping) adj (density or	USPAT;	2004/09/02
]		concentration)) near10 (equal or	US-PGPUB;	16:56
	:	similar)).ti,ab,clm. and junction.ti,ab,clm.	EPO; JPO;	
		and diode.ti,ab,clm. and	DERWENT;	
		polysilicon.ti,ab,clm.	IBM_TDB	
178	1	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or	US-PGPUB;	16:57
		similar)).ti,ab,clm. and junction.ti,ab,clm.	EPO; JPO;	
1		and diode.ti,ab,clm. and polysilicon	DERWENT;	
			IBM_TDB	
180	9	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or similar or	US-PGPUB;	16:58
		substantially)).ti,ab,clm. and	EPO; JPO;	
		junction.ti,ab,clm. and diode.ti,ab,clm. and	DERWENT;	
		polysilicon	IBM_TDB	

181	1	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or similar or	US-PGPUB;	16:59
		substantially)).ti,ab,clm. and	EPO; JPO;	
		junction.ti,ab,clm. and diode.ti,ab,clm. and	DERWENT;	
		(polysilicon near5 (plug or trench or via or	IBM_TDB	
		hole or opening))		
183	1	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or similar or	US-PGPUB;	17:00
		substantially)) and junction.ti,ab,clm. and	EPO; JPO;	
		diode.ti,ab,clm. and (polysilicon near5 (plug	DERWENT;	
		or trench or via or hole or	IBM_TDB	
		opening)).ti,ab,clm.		
182	7	(((impurity or doping) adj (density or	USPAT;	2004/09/02
		concentration)) near10 (equal or similar or	US-PGPUB;	17:00
		substantially)) and junction.ti,ab,clm. and	EPO; JPO;	
		diode.ti,ab,clm. and (polysilicon near5 (plug	DERWENT;	
		or trench or via or hole or opening))	IBM_TDB	
184	40	(US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	17:01
		US-6352882-\$ or US-6121661-\$ or	JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT	
		US-6204518-\$ or US-5962900-\$ or		
		US-5907778-\$ or US-5686736-\$ or		
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
	:	US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$ or		
		US-5119148-\$).did. or (US-20010045665-\$ or		
		US-20020031916-\$ or US-20020057594-\$ or		
		US-20020125541-\$ or US-20020043687-\$ or		
		US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.		

185	4	((US-5942933-\$ or US-5386138-\$ or	USPAT;	2004/09/02
		US-6333535-\$ or US-6545360-\$ or	US-PGPUB;	17:02
		US-6352882-\$ or US-6121661-\$ or	EPO; JPO;	
		US-5160987-\$ or US-6587370-\$ or	DERWENT;	
		US-6204518-\$ or US-5962900-\$ or	IBM_TDB	
		US-5907778-\$ or US-5686736-\$ or	_	
		US-5266831-\$ or US-6320474-\$ or		
		US-4169270-\$ or US-4103415-\$ or		
		US-5891778-\$ or US-4958209-\$ or		
		US-6759700-\$ or US-6692998-\$ or		
		US-6455378-\$ or US-5666077-\$ or		
		US-5422299-\$ or US-4300212-\$ or		
		US-5119148-\$).did. or (US-20010045665-\$ or		
		US-20020031916-\$ or US-20020057594-\$ or	1	
		US-20020125541-\$ or US-20020043687-\$ or		
		US-20020074483-\$ or		
		US-20020063288-\$).did. or (JP-05283715-\$		
		or JP-07245344-\$ or JP-04069939-\$ or		
		JP-04034982-\$).did. or (US-5386138-\$ or		
		JP-05283715-\$ or JP-2001257349-\$ or		
		GB-2218565-\$).did.) and ((substantially or		
-		equal or similar or identical) near5 (density		
		or concentration))		
186	0	((substantially or equal or similar or	USPAT;	2004/09/02
		identical) near5 (density or concentration))	US-PGPUB;	17:03
		and (polysilicon near plug) and (((p-n) or pn)	EPO; JPO;	
		near junction near diode)	DERWENT;	
i			IBM_TDB	
187	0	((substantially or equal or similar or	USPAT;	2004/09/02
		identical) near5 (density or concentration))	US-PGPUB;	17:03
		and (polysilicon near (trench or plug)) and	EPO; JPO;	
		(((p-n) or pn) near junction near diode)	DERWENT;	
			IBM_TDB	
188	3	((substantially or equal or similar or	USPAT;	2004/09/02
		identical) near5 (density or concentration))	US-PGPUB;	17:05
		and (polysilicon near3 (trench or plug)) and	EPO; JPO;	
		(((p-n) or pn) near junction near diode)	DERWENT;	
			IBM_TDB	
189	7	((substantially or equal or similar or	USPAT;	2004/09/02
		identical) near5 (density or concentration))	US-PGPUB;	17:05
		and (polysilicon near3 (trench or plug)) and	EPO; JPO;	
		(((p-n) or pn) near2 junction near2 diode)	DERWENT;	
	_		IBM_TDB	

L	Hits	Search Text	DB	Time stamp
Number				
132	45	((impurity or doping) near (density or	USPAT;	2004/09/02
		concentration)) and ((junction near diode)	US-PGPUB;	16:30
		with polysilicon)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
133	8	((impurity or doping) near (density or	USPAT;	2004/09/02
		concentration)) and ((junction near diode)	US-PGPUB;	16:31
		with polysilicon with (trench or via or hole	EPO; JPO;	
		or plug))	DERWENT;	
			IBM_TDB	
134	50289	((p-n) or pn) adj junction	USPAT;	2004/09/02
			US-PGPUB;	16:32
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
135	892	(((p-n) or pn) adj junction) and (polysilicon	USPAT;	2004/09/02
		near3 (plug or via or hole or trench))	US-PGPUB;	16:32
			EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
136	54	(((p-n) or pn) adj junction).ti,ab,clm. and	USPAT;	2004/09/02
		(polysilicon near3 (plug or via or hole or	US-PGPUB;	16:33
		trench)).ti,ab,clm.	EPO; JPO;	
		,, , ,	DERWENT;	
			IBM_TDB	
137	8	(((p-n) or pn) adj junction).ti,ab,clm. and	USPAT;	2004/09/02
		(polysilicon near3 (plug or via or hole or	US-PGPUB;	16:36
		trench)).ti,ab,clm. and diode.ti,ab,clm.	EPO; JPO;	
		, ,	DERWENT;	
			IBM_TDB	
138	0	(((p-n) or pn) adj junction).ti,ab,clm. and	USPAT;	2004/09/02
		(polysilicon near3 (plug or via or hole or	US-PGPUB;	16:36
		trench) near3 type).ti,ab,clm. and	EPO; JPO;	
		diode.ti,ab,clm.	DERWENT;	
			IBM_TDB	
139	1	(((p-n) or pn) adj junction).ti,ab,clm. and	USPAT;	2004/09/02
	•	(polysilicon near3 (plug or via or hole or	US-PGPUB;	16:36
		trench) near3 (doped or type)).ti,ab,clm.	EPO; JPO;	.0.50
		and diode.ti,ab,clm.	DERWENT;	
		unu uivueitijapjeiiii	IBM_TDB	

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